

FDC6506P

Dual P-Channel Logic Level PowerTrench™ MOSFET

General Description

These P-Channel logic level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

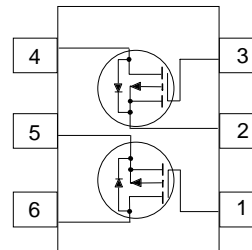
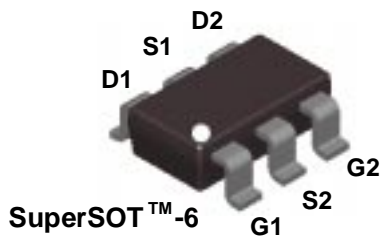
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the bigger more expensive SO-8 and TSSOP-8 packages are impractical.

Applications

- Load switch
- Battery protection
- Power management

Features

- -1.8 A, -30 V. $R_{DS(on)} = 0.170 \Omega @ V_{GS} = -10 \text{ V}$
 $R_{DS(on)} = 0.280 \Omega @ V_{GS} = -4.5 \text{ V}$
- Low gate charge (2.3nC typical).
- Fast switching speed.
- High performance trench technology for extremely low $R_{DS(on)}$.
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	-30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (Note 1a) - Pulsed	-1.8	A
		-10	
P _D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	0.96	W
		0.9	
		0.7	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	130	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	60	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.506	FDC6506P	7"	8mm	3000 units

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = -250 μA	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = -250 μA, Referenced to 25°C		-20		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -24 V, V _{GS} = 0 V			-1	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA

On Characteristics (Note 2)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-1	-1.8	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = -250 μA, Referenced to 25°C		4		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -1.8 A V _{GS} = -10 V, I _D = -1.8 A @ 125°C V _{GS} = -4.5 V, I _D = -1.4 A		0.14 0.20 0.22	0.17 0.27 0.28	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = -10 V, V _{DS} = -5 V	-10			A
g _{FS}	Forward Transconductance	V _{DS} = -5 V, I _D = -1.8 A		3		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = -15 V, V _{GS} = 0 V, f = 1.0 MHz		190		pF
C _{oss}	Output Capacitance			70		pF
C _{rss}	Reverse Transfer Capacitance			30		pF

Switching Characteristics (Note 2)

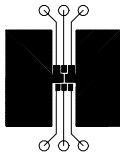
t _{d(on)}	Turn-On Delay Time	V _{DD} = -15 V, I _D = -1 A, V _{GS} = -4.5 V, R _{GEN} = 6 Ω		7	14	ns
t _r	Turn-On Rise Time			8	16	ns
t _{d(off)}	Turn-Off Delay Time			14	25	ns
t _f	Turn-Off Fall Time			2	6	ns
Q _g	Total Gate Charge	V _{DS} = -5 V, I _D = -1.8 A, V _{GS} = -10 V		2.3	3.5	nC
Q _{gs}	Gate-Source Charge			1		nC
Q _{gd}	Gate-Drain Charge			0.8		nC

Drain-Source Diode Characteristics and Maximum Ratings

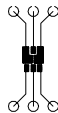
I _S	Maximum Continuous Drain-Source Diode Forward Current			-0.8	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -0.8 A <small>(Note 2)</small>		-0.8	-1.2	V

Notes:

- R_{θJA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θJA} is determined by the user's board design. Both devices are assumed to be operating and sharing the dissipated heat energy equally.



a) 130 °C/W when mounted on a 0.125 in² pad of 2 oz. copper.



b) 140 °C/W when mounted on a 0.005 in² pad of 2 oz. copper.



c) 180 °C/W when mounted on a 0.0015 in² pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Typical Characteristics

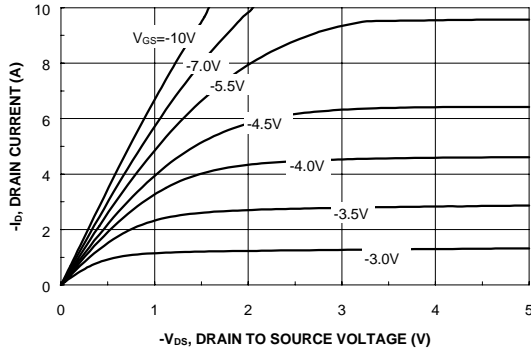


Figure 1. On-Region Characteristics.

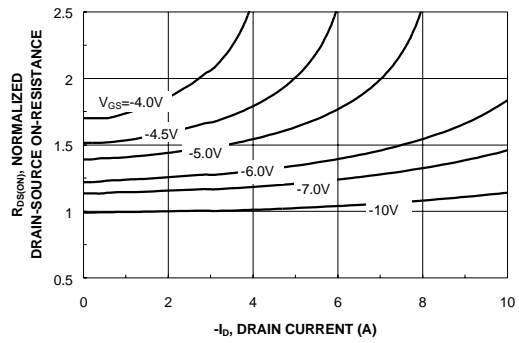


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

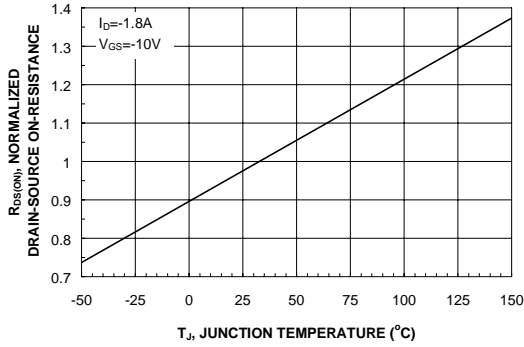


Figure 3. On-Resistance Variation with Temperature.

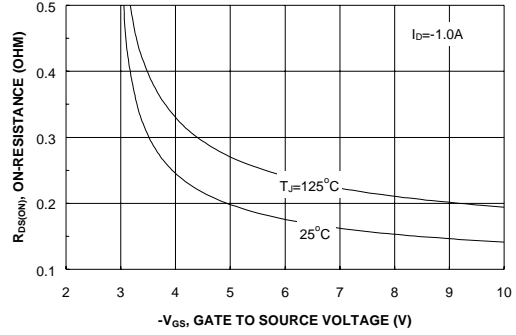


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

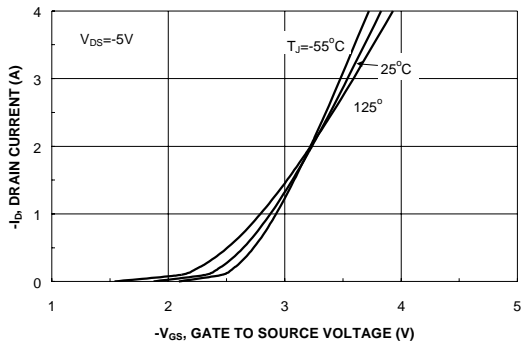


Figure 5. Transfer Characteristics.

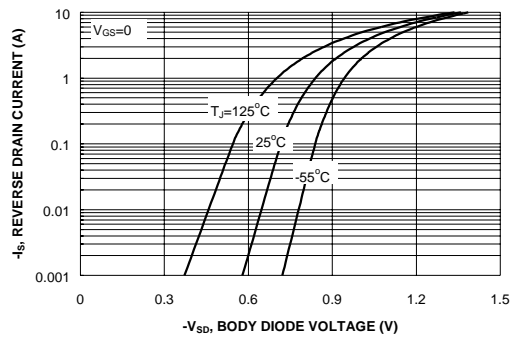


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

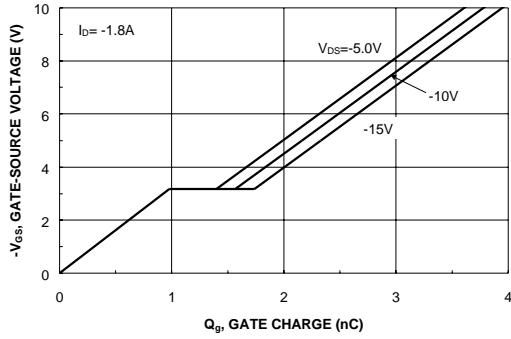


Figure 7. Gate-Charge Characteristics.

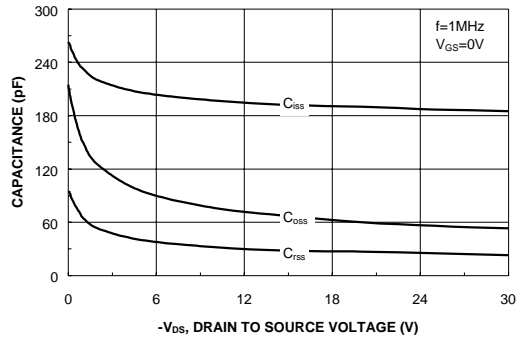


Figure 8. Capacitance Characteristics.

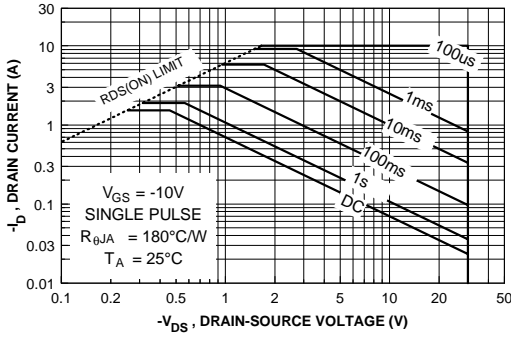


Figure 9. Maximum Safe Operating Area.

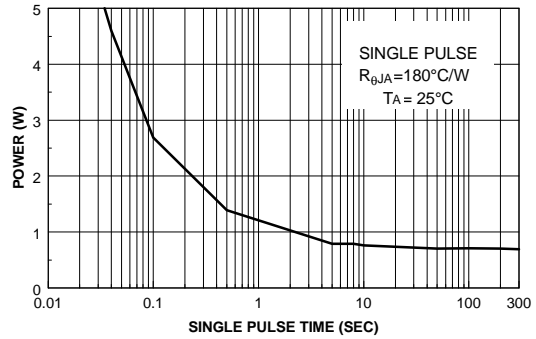


Figure 10. Single Pulse Maximum Power Dissipation.

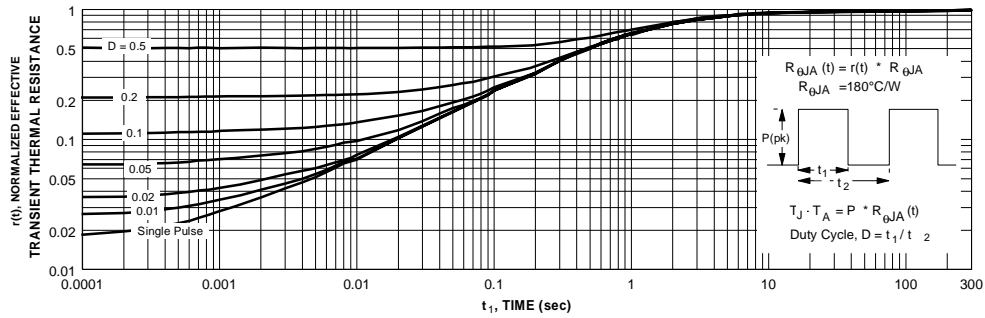
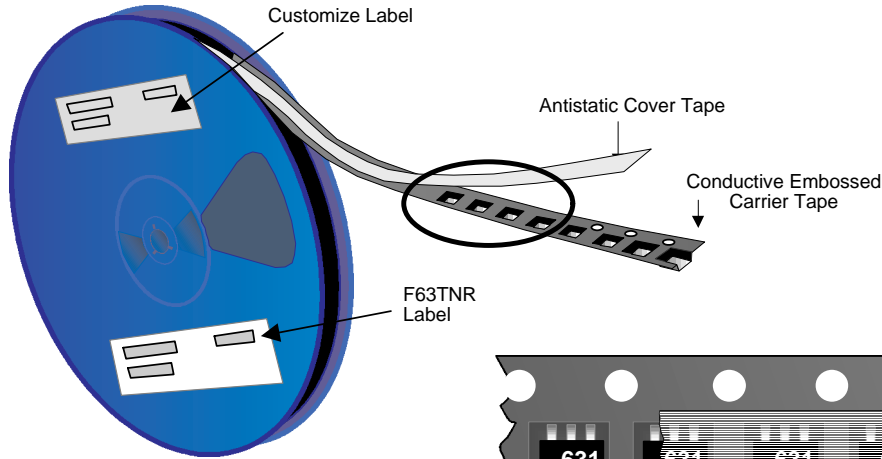


Figure 11. Transient Thermal Response Curve.

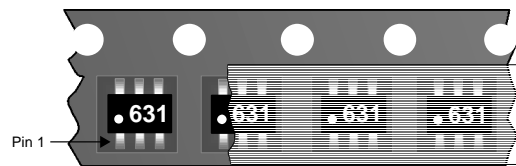
Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

SuperSOT™-6 Tape and Reel Data and Package Dimensions

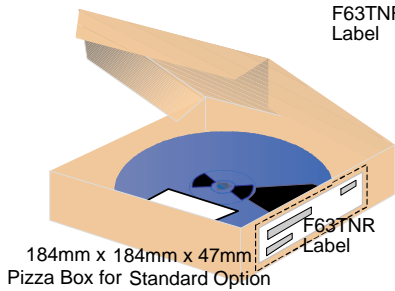
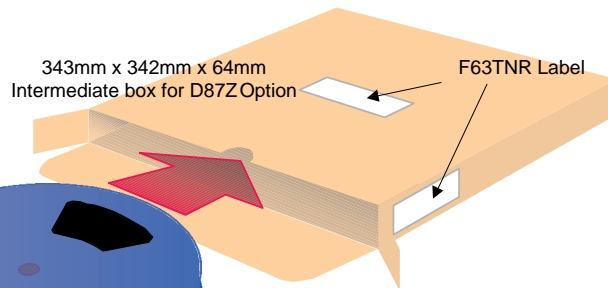
SSOT-6 Packaging
Configuration: Figure 1.0



SSOT-6 Packaging Information		
Packaging Option	Standard (no flow code)	D87Z
Packaging type	TNR	TNR
Qty per Reel/Tube/Bag	3,000	10,000
Reel Size	7" Dia	13"
Box Dimension (mm)	184x187x47	343x343x64
Max qty per Box	9,000	20,000
Weight per unit (gm)	0.0158	0.0158
Weight per Reel (kg)	0.1440	0.4700
Note/Comments		



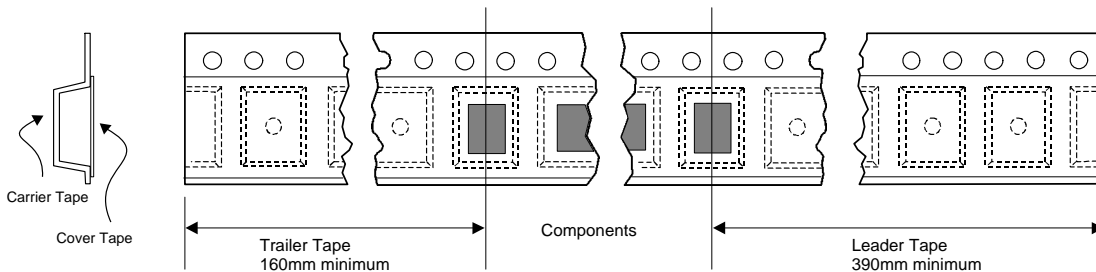
SSOT-6 Unit Orientation



F63TNR Label sample

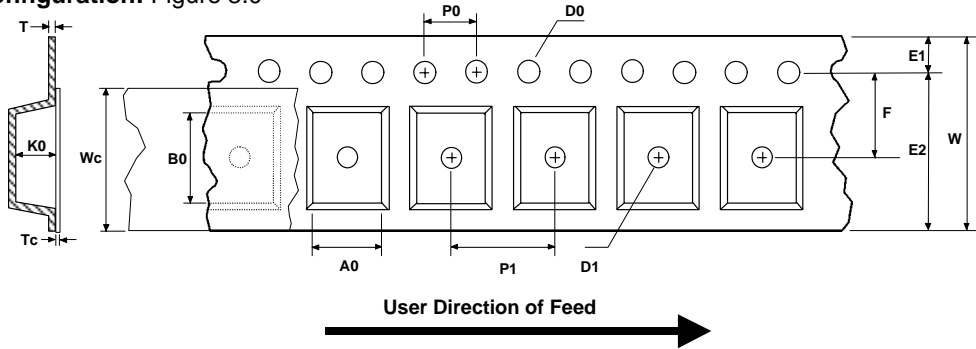


SSOT-6 Tape Leader Trailer
Configuration: Figure 2.0



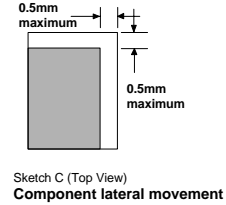
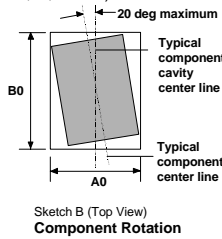
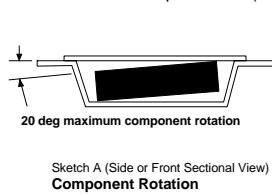
SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

SSOT-6 Embossed Carrier Tape Configuration: Figure 3.0

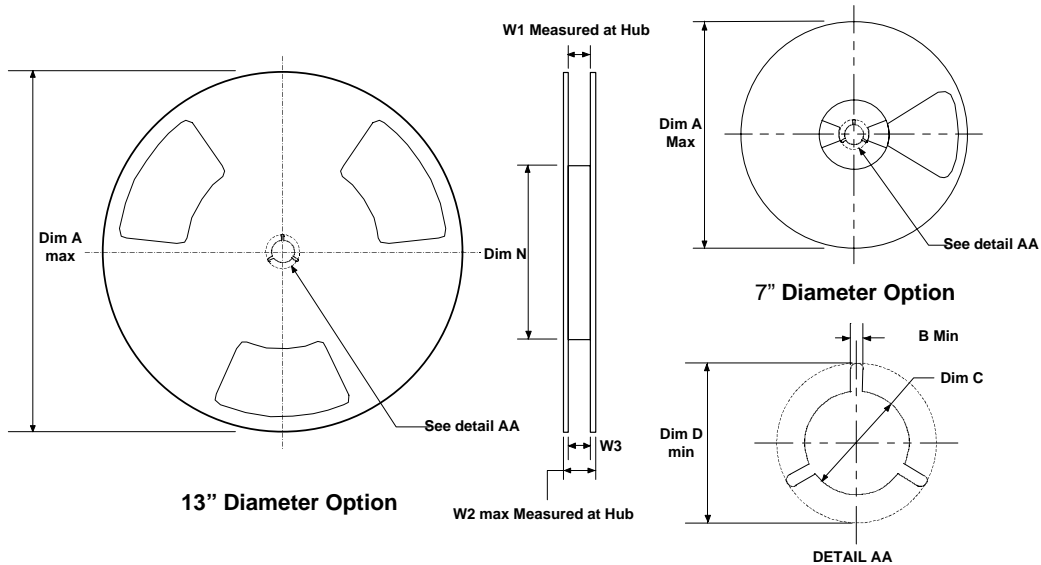


Dimensions are in millimeter														
Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.00 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



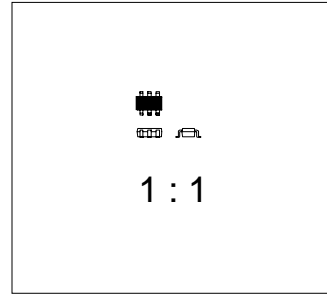
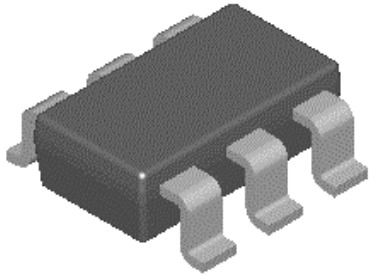
SSOT-6 Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

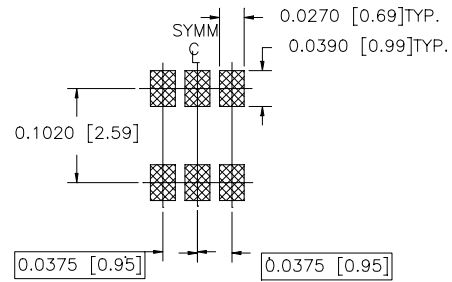
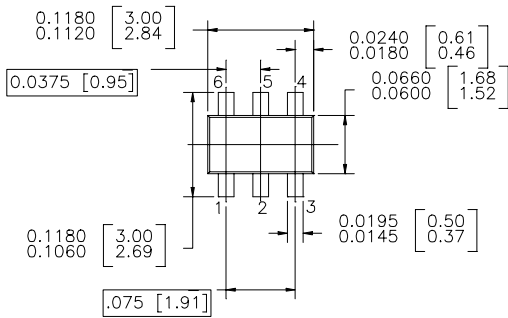
SuperSOT™-6 (FS PKG Code 31, 33)



Scale 1:1 on letter size paper

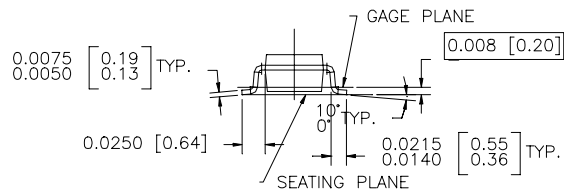
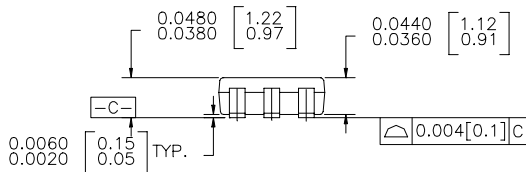
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0158



LAND PATTERN RECOMMENDATION

CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS



SUPER SOT 6 LEADS

NOTES : UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICRONS 93.81 MICROMETERS)
MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

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FACT™	QS™
FACT Quiet Series™	Quiet Series™
FAST®	SuperSOT™-3
FASTr™	SuperSOT™-6
GTO™	SuperSOT™-8
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.